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The invention relates to processes for thermal treatment of semiconductor materials and may be used in microelectronics.

Summary of the invention consists in the modification of near-surface layers of zinc selenide monocrystals, including the thermal treatment of monocrystals in the bismuth melt with additive of 0.02...1.10 at.% of chrome at the temperature of 1000...1200°C during 60...150 hours.

The result consists in extending the functional possibilities of the devices obtained on base of zinc selenide monocrystals doped with chrome from bismuth melt, as well as in improving the stoichiometry in the doping process.

Claims: 1

Fig.: 2